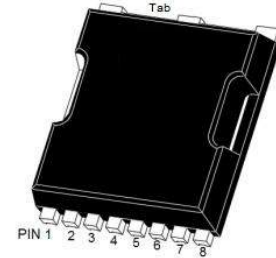


■ **PRODUCT CHARACTERISTICS**

VDSS	40V
$R_{DS(on)}$ typ(@ $V_{GS} = 4.5$ V)	2m Ω
$R_{DS(on)}$ typ(@ $V_{GS} = 10$ V)	1.05m Ω
ID	300A

■ **FEATURES**

Surface-mounted package Advanced
terch cell design Super trench

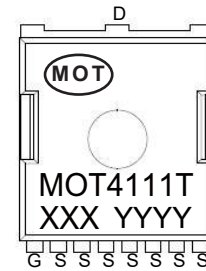


TOLL-8L

■ **APPLICATIONS**

High power system inverter
Light electric vehicles
BMS
Drones

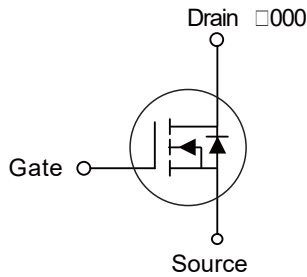
Pin configuration (Top view)



XXX = Lot Number
YYYY = Year Week

Marking

■ **SYMBOL**



Order information

Device	Package	Shipping
MOT4111T/TR	TOLL-8L	2000/Tape&Reel

■ ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Max	Unit
Drain-Source Voltage	V _{DS}	T _C = 25 °C	40	-	V
Gate-Source Voltage	V _{GS}	T _C = 25 °C	-	±20	V
Drain Current (DC) *	I _D	T _C = 25 °C, V _{GS} = 10 V	-	300	A
		T _C = 100 °C, V _{GS} = 10 V	-	200	A
Drain Current (Pulsed) ***	I _{DM}	T _C = 25 °C, V _{GS} = 10 V	-	1200	A
Drain power dissipation	P _{tot}	T _C = 25 °C	-	500	W
Storage Temperature	T _{stg}		-55	150	°C
Junction Temperature	T _J		-	150	°C
Continuous-Source Current	I _S	T _C = 25 °C	-	300	A
Single Pulsed Avalanche Energy	E _{AS}	V _{DD} = 40V , L= 1 mH	-	1352	mJ
Thermal Resistance- Junction to Ambient**	R _{θJA}		-	32.8	°C/W
Thermal Resistance- Junction to Case**	R _{θJC}		-	0.25	

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

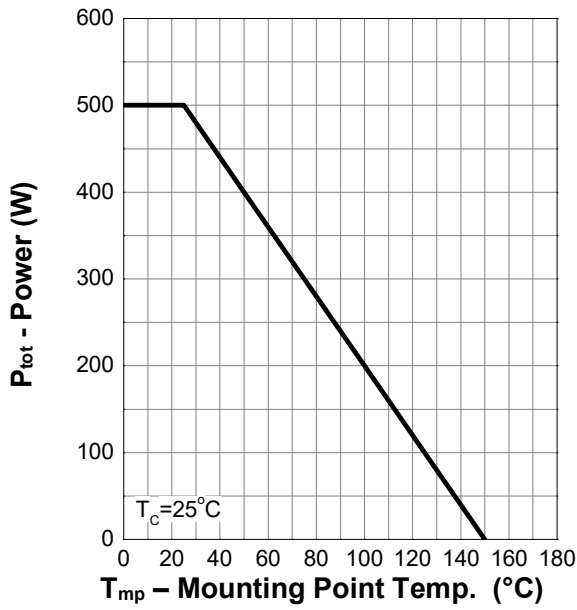
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0 V, I _{DS} = 250 μA	40	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _{DS} = 250 μA	1	1.7	3	V
Drain Leakage Current	I _{DSS}	V _{DS} = 32 V, V _{GS} = 0 V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = 0 V, V _{GS} = ± 20 V	-	-	±100	nA
On-State Resistance ^a	R _{DS(ON)}	V _{GS} = 10 V, I _{DS} = 30A	-	1.05	1.1	mΩ
		V _{GS} = 4.5 V, I _{DS} = 30A	-	2.0	2.5	
Diode Characteristics						
Diode Forward Voltage ^a	V _{SD}	I _{SD} = 50A, V _{GS} = 0 V	-	-	1.3	V
Reverse Recovery Time	t _{rr}	I _{DS} = 50A, V _{GS} = 0 V dI _{SD} /dt = 100 A/μs	-	25	-	nS
Reverse Recovery Charge	Q _{rr}		-	20	-	nC
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 20 V Frequency = 1 MHz	-	13725	-	pF
Output Capacitance	C _{oss}		-	1031	-	
Reverse Transfer Capacitance ^b	C _{rss}		-	321	-	
Turn-on Delay Time	t _{d(on)}	V _{DS} = 20 V, V _{GEN} = 10 V, R _G = 3.9 Ω, R _L = 0.4 Ω, I _{DS} = 50A	-	32	-	nS
Turn-on Rise	t _r		-	140	-	
Turn-off Delay Time	t _{d(off)}		-	179	-	
Turn-off Fall Time	t _f		-	120	-	
Gate Charge Characteristics^b						
Total Gate Charge	Q _g	V _{DS} = 20 V, V _{GS} = 10 V, I _{DS} = 50A	-	231	-	nC
Gate-Source Charge	Q _{gs}		-	58	-	
Gate-Drain Charge	Q _{gd}		-	33	-	

Notes :

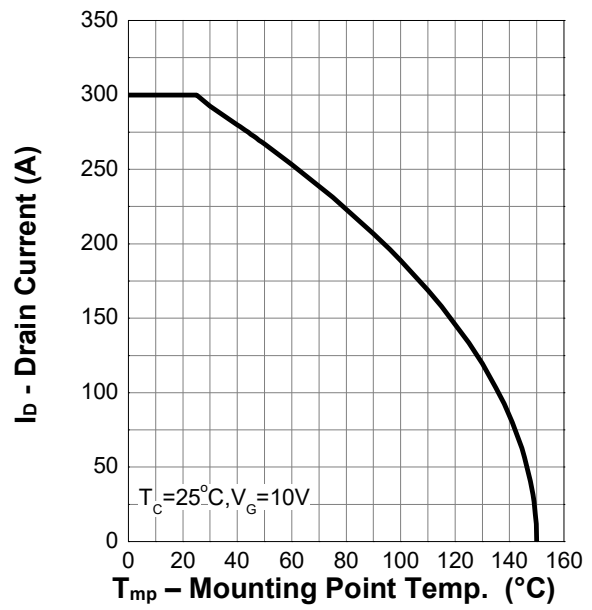
- * Pulse width ≤ 300 μs, duty cycle ≤ 2 %
- ** Surface Mounted on minimum footprint pad area.
- *** Limited by bonding wire
- a : Pulse test ; pulse width ≤ 300 μs, duty cycle ≤ 2%
- b : Guaranteed by design, not subject to production testing

■ TYPICAL CHARACTERISTICS

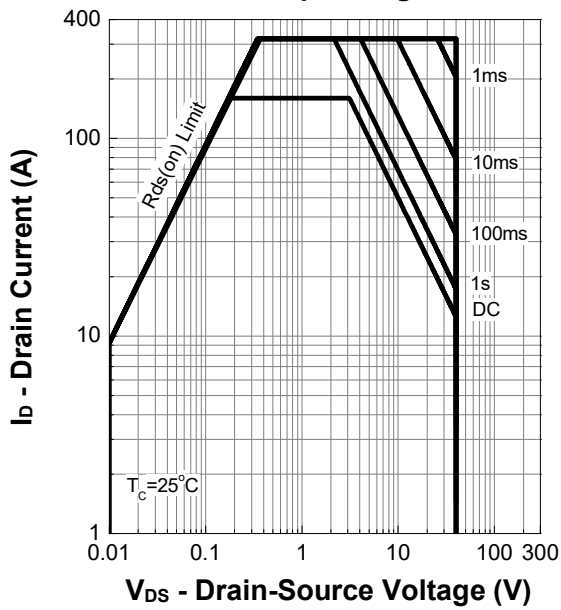
Power Capability



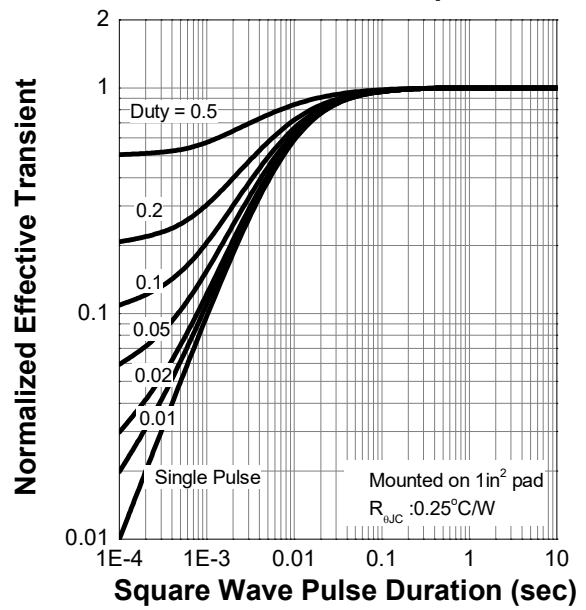
Current Capability



Safe Operating Area

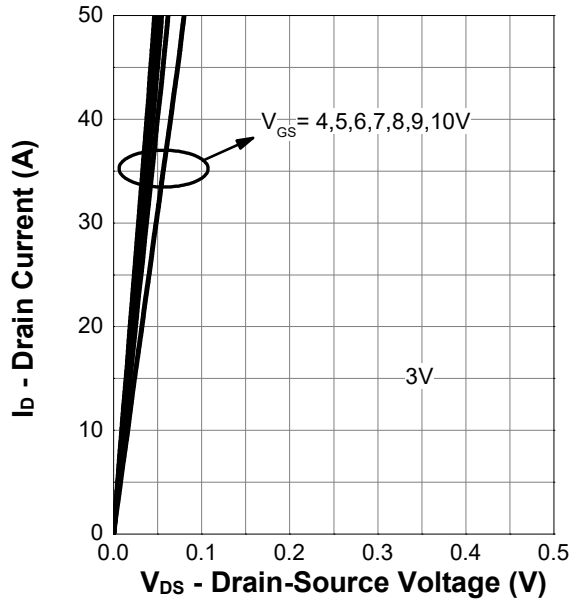


Transient Thermal Impedance

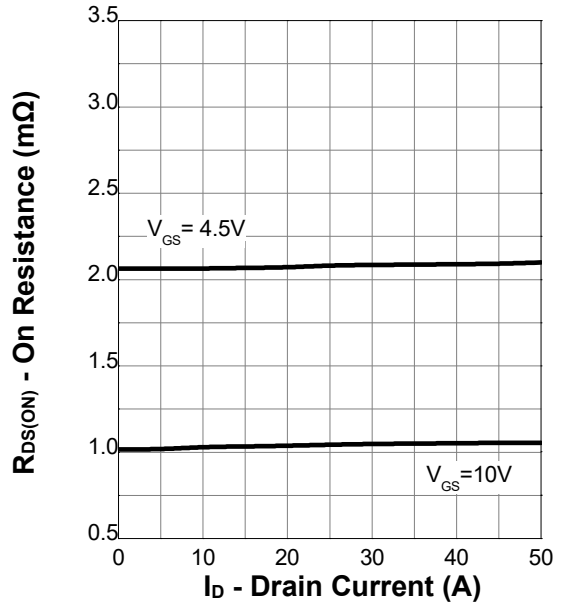


■ TYPICAL CHARACTERISTICS(Cont.)

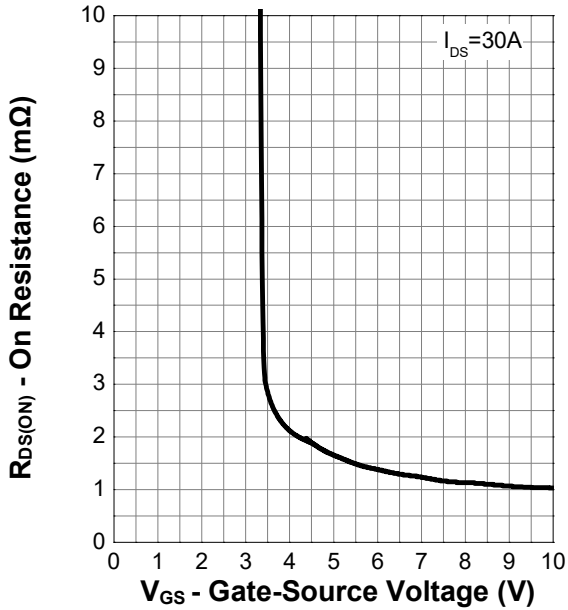
Output Characteristics



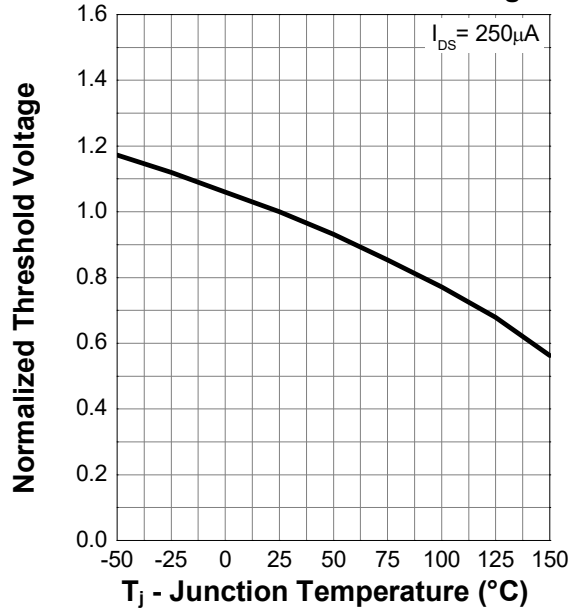
On Resistance



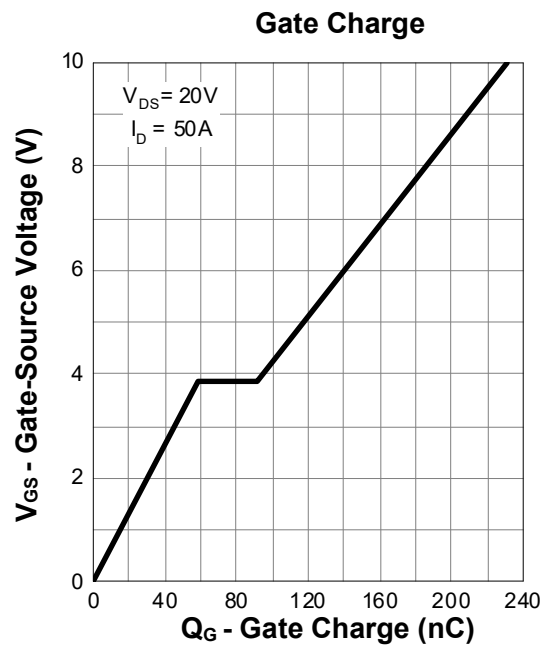
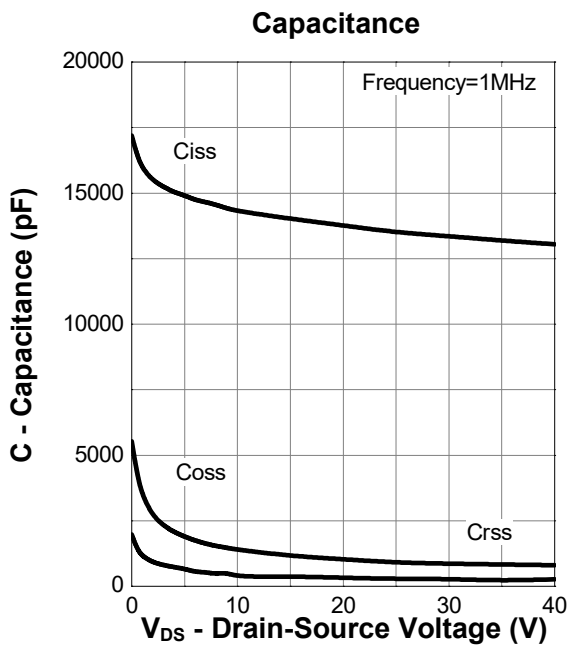
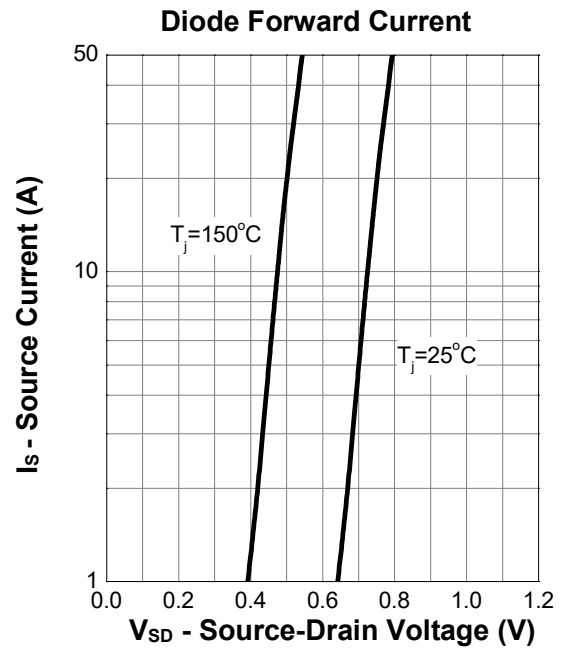
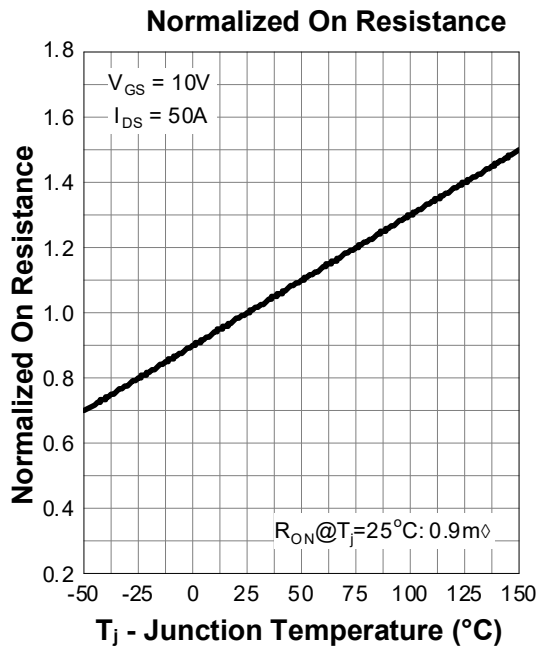
Transfer Characteristics



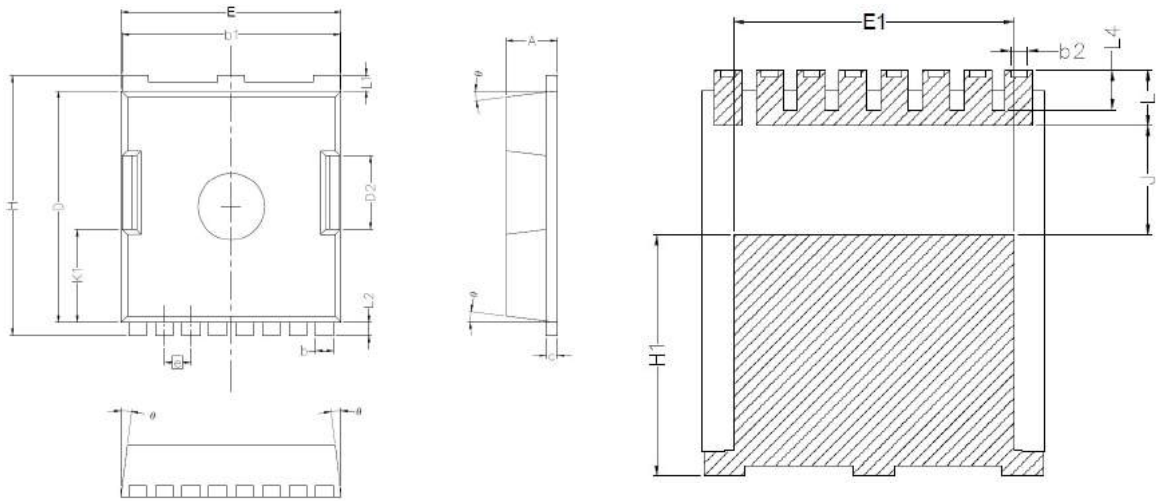
Normalized Threshold Voltage



■ TYPICAL CHARACTERISTICS(Cont.)



■ TOLL-8L PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.42	0.50
c	0.40	0.60
D	10.28	10.58
D2	3.10	3.50
E	9.70	10.10
E1	7.90	8.30
e	1.20BSC	
H	11.48	11.88
H1	6.75	7.15
N	8	
J	3.00	3.30
K1	3.98	4.38
L	1.40	1.80
L1	0.60	0.80
L2	0.50	0.70
L4	1.00	1.30
θ	4°	10°

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